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# FC6B21150L1

## Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

### ■ Features

- Low source-source ON resistance:  $R_{ss(on)}$  typ. = 4.3 mΩ (VGS = 3.8 V)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL: Level 1 compliant)

### ■ Marking Symbol: 16

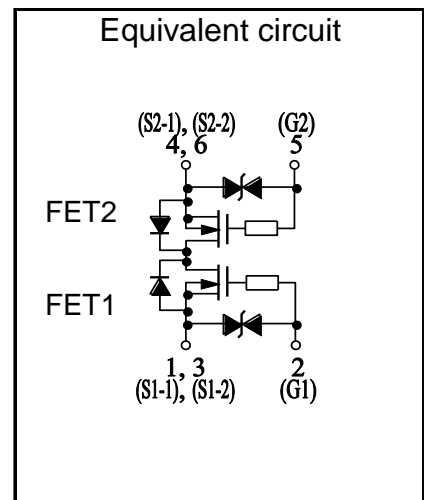
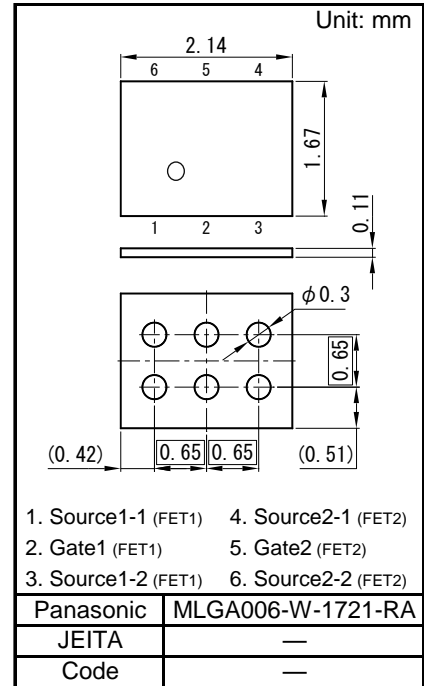
### ■ Packaging

Embossed type (Thermo-compression sealing) : 1 000 pcs / reel (standard)

### ■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	12	V
Gate-source Voltage <sup>*3</sup>	VGS	±10.5	V
Source Current	DC <sup>*1</sup>	IS1	8
	DC <sup>*2</sup>	IS2	17
	Pulse <sup>*3</sup>	ISp	80
Total Power Dissipation	DC <sup>*1</sup>	PD1	0.45
	DC <sup>*2</sup>	PD2	2.1
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Thermal resistance (ch-a)	DC <sup>*1</sup>	Rth1	278
	DC <sup>*2</sup>	Rth2	59

- Note \*1 Mounted on FR4 board  
 (25.4mm × 25.4mm × t1.0mm, 36μm Copper)  
 \*2 Mounted on Ceramic substrate  
 (70 mm × 70 mm × t1.0 mm).  
 \*3 t = 10 μs, Duty Cycle ≤ 1 %



■ Electrical Characteristics Ta = 25 °C ± 3 °C

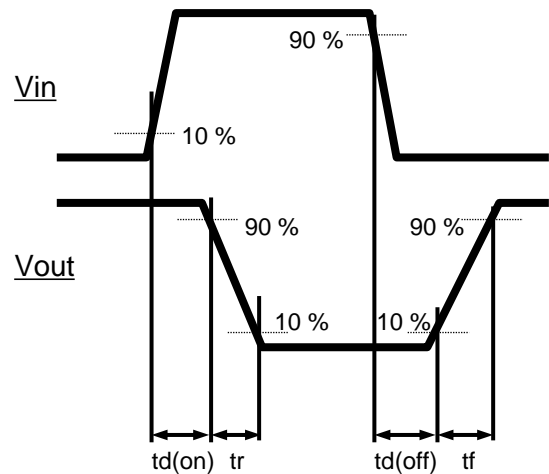
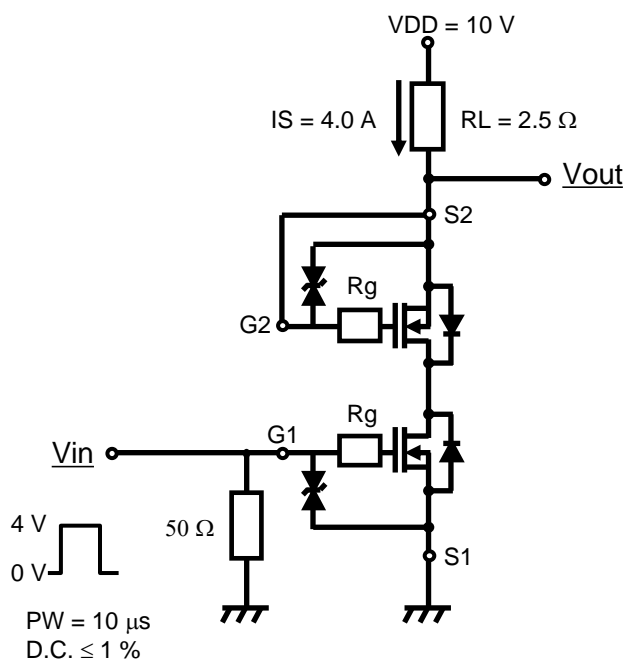
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μA
Gate-source Leakage Current	IGSS	VGS = ±8 V, VSS = 0 V			±10	μA
		VGS = ±5 V, VSS = 0 V			±1.0	
Gate-source Threshold Voltage	Vth	IS = 0.84 mA, VSS = 10 V	0.35	0.90	1.4	V
Source-source On-state Resistance	RSS(on)1	IS = 4.0 A, VGS = 4.5 V	3	4	5.1	mΩ
	RSS(on)2	IS = 4.0 A, VGS = 3.8 V	3.2	4.3	5.5	
	RSS(on)3	IS = 4.0 A, VGS = 3.1 V	3.5	4.8	6.8	
	RSS(on)4	IS = 4.0 A, VGS = 2.5 V	3.8	5.9	10	
Body Diode Forward Voltage	VF(s-s)	IF = 4.0 A, VGS = 0 V		0.8	1.2	V
Input Capacitance <sup>*1</sup>	Ciss	VSS = 10 V, VGS = 0 V, f = 1 MHz		2760		pF
Output Capacitance <sup>*1</sup>	Coss			450		
Reverse Transfer Capacitance <sup>*1</sup>	Crss			390		
Turn-on delay Time <sup>*1,*2</sup>	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		4.1		μs
Rise Time <sup>*1,*2</sup>	tr	IS = 4.0 A		5.2		
Turn-off delay Time <sup>*1,*2</sup>	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		12.9		μs
Fall Time <sup>*1,*2</sup>	tf	IS = 4.0 A		8.3		
Total Gate Charge <sup>*1</sup>	Qg	VDD = 10 V		26		nC
Gate-source Charge <sup>*1</sup>	Qgs	VGS = 0 to 4.0 V,		9		
Gate-drain Charge <sup>*1</sup>	Qgd	IS = 4.0 A		8		

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

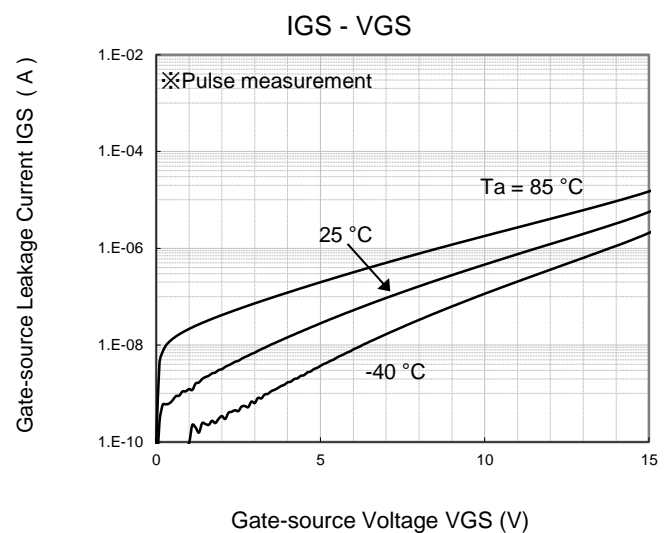
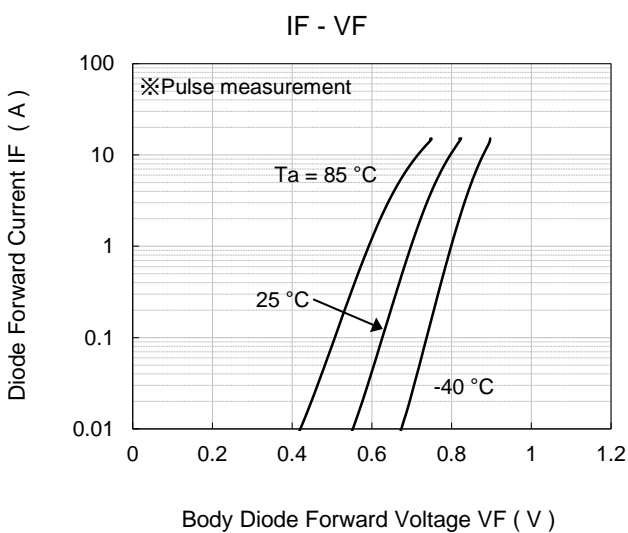
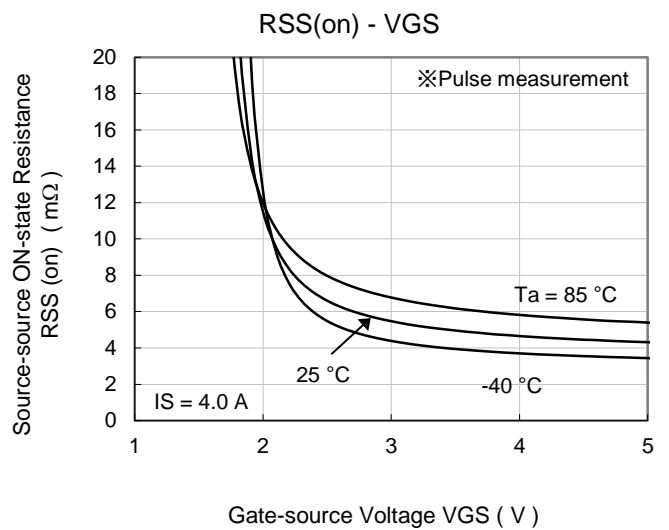
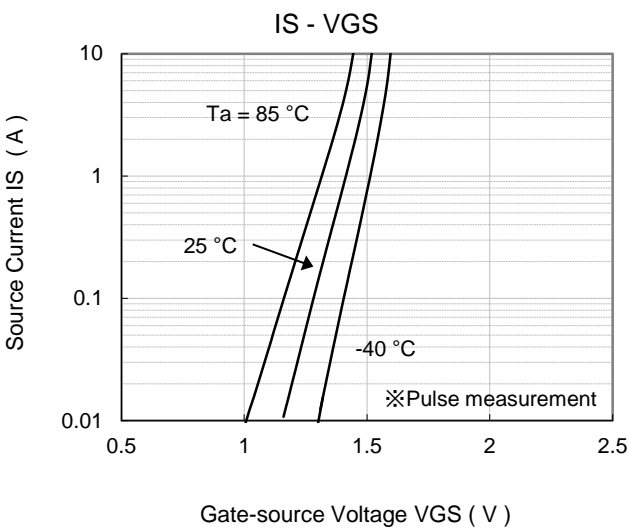
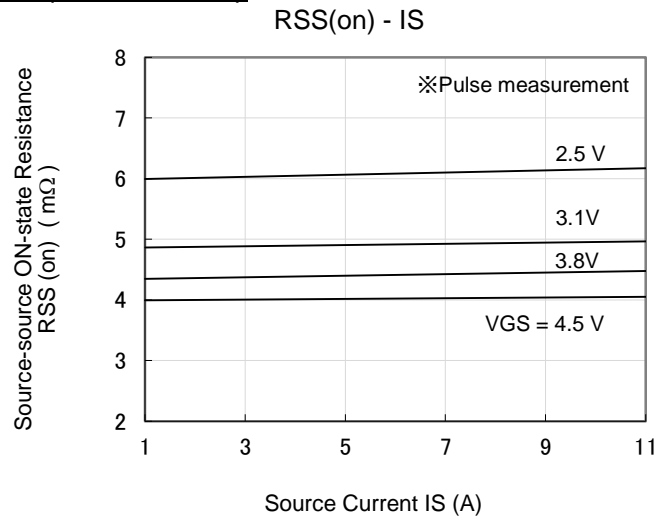
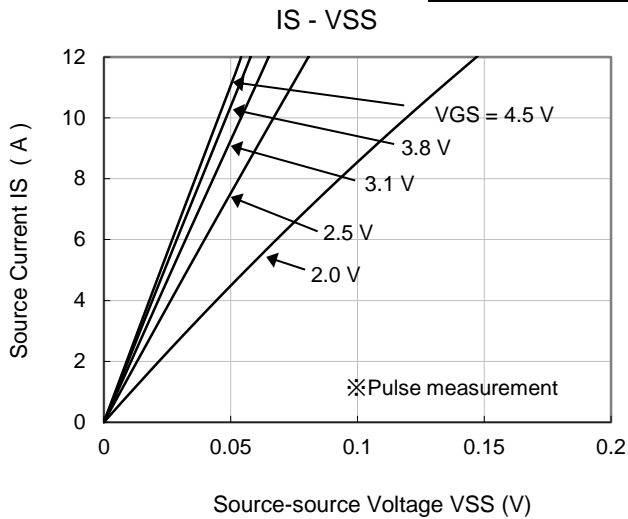
\*1 Guaranteed by design, not subject to production testing

\*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

Note2 : Measurement circuit

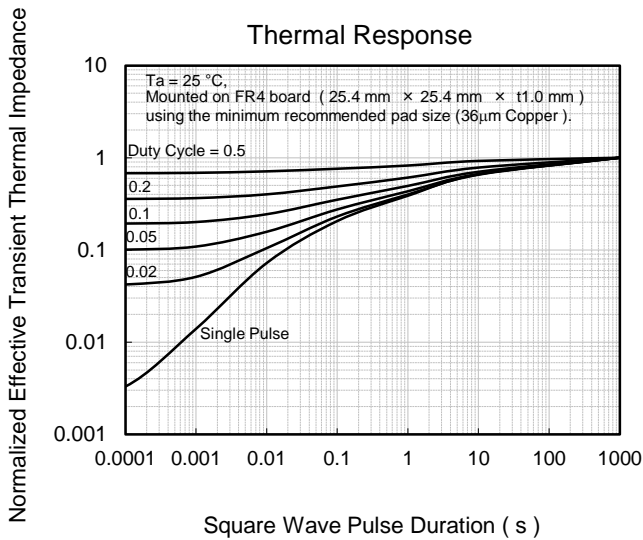
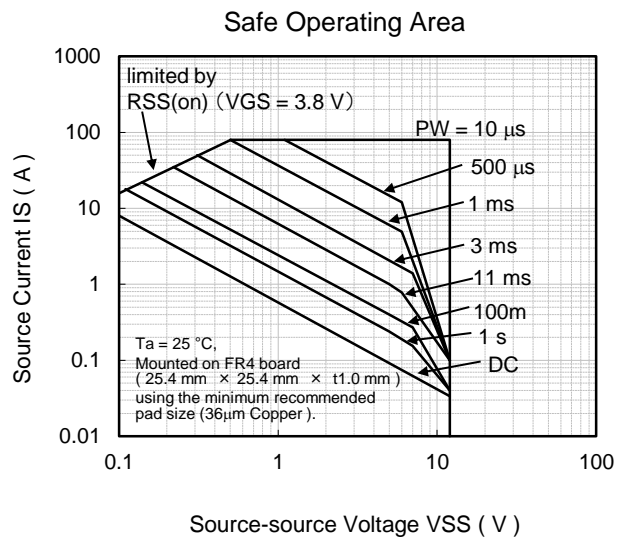
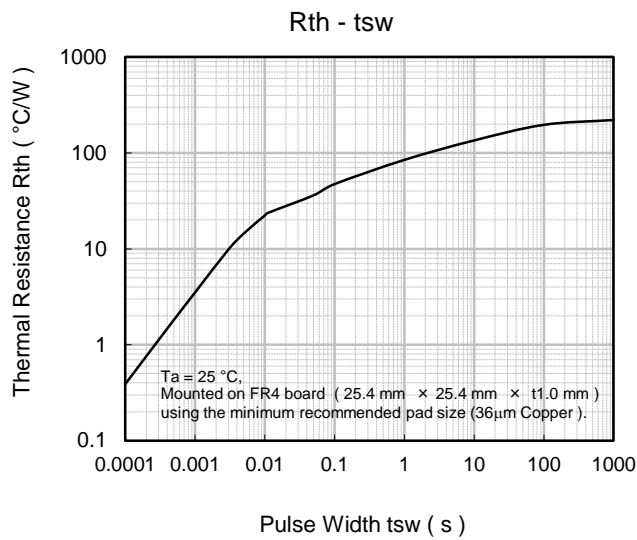
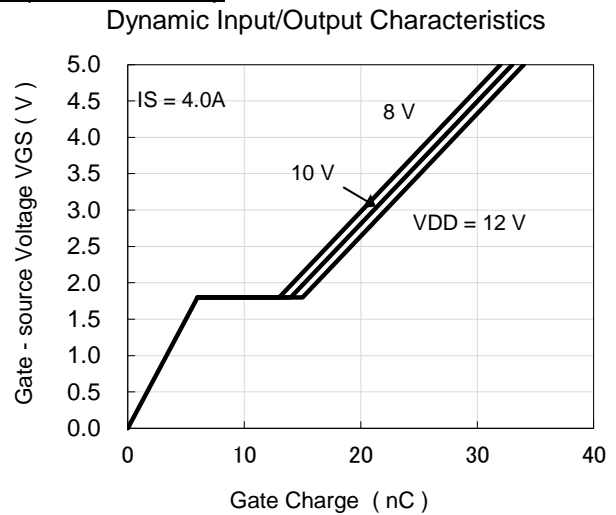
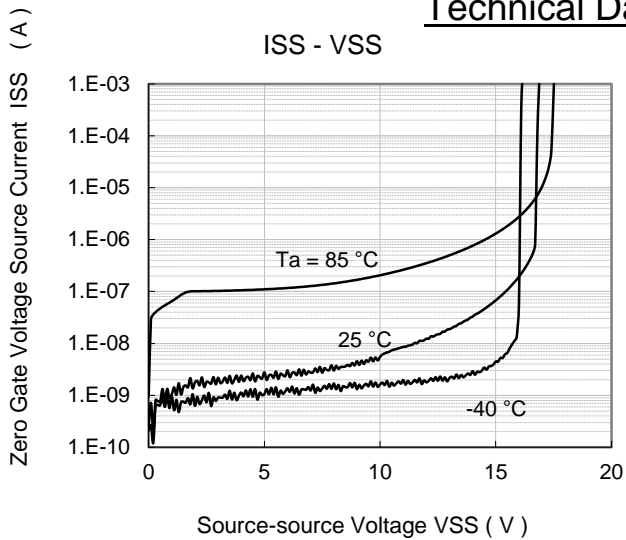


Technical Data ( reference )



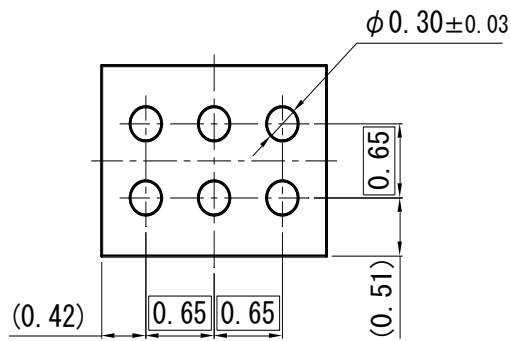
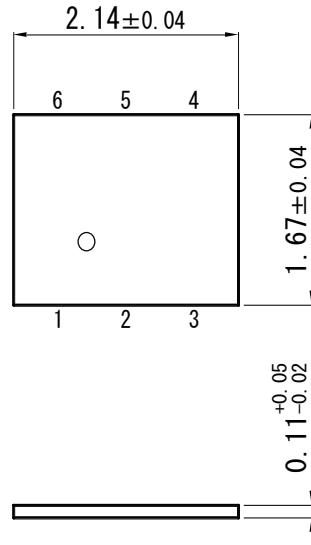


Technical Data ( reference )



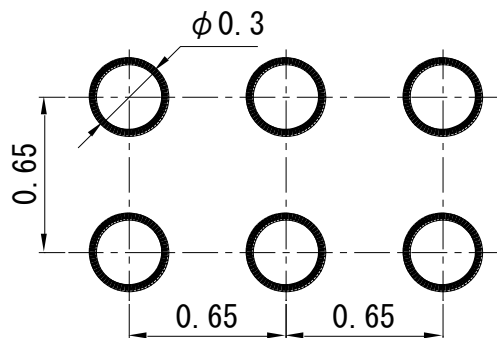
■ Outline (MLGA006-W-1721-RA)

Unit: mm



■ Land Pattern (Reference)

Unit: mm



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